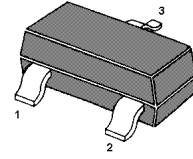


MMBTSA6571

PNP Silicon Epitaxial Planar Transistor

for general amplifier applications.



1. Base 2. Emitter 3. Collector
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	60	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	7	V
Collector Current	$-I_C$	100	mA
Peak Collector Current	$-I_{CP}$	200	mA
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ	Max.	Unit
DC Current Gain at $-V_{CE} = 10\text{ V}$, $-I_C = 2\text{ mA}$	h_{FE}	160	-	260	-
Current Gain Group Q R S	h_{FE}	210	-	340	-
	h_{FE}	290	-	460	-
	h_{FE}				
Collector Base Cutoff Current at $-V_{CB} = 50\text{ V}$	$-I_{CBO}$	-	-	10	nA
Collector Emitter Cutoff Current at $-V_{CE} = 50\text{ V}$	$-I_{CEO}$	-	-	100	μA
Emitter Base Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	-	-	10	nA
Collector Base Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage at $-I_C = 2\text{ mA}$	$-V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage at $-I_E = 10\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	7	-	-	V
Collector Emitter Saturation Voltage at $-I_C = 100\text{ mA}$, $-I_B = 10\text{ mA}$	$-V_{CE(sat)}$	-	-	0.5	V
Current Gain Bandwidth Product at $-V_{CB} = 10\text{ V}$, $I_E = 1\text{ mA}$, $f = 200\text{ MHz}$	f_T	-	80	-	MHz
Collector Output Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	2.7	-	pF

